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**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claim 1-7 (canceled)

8. (currently amended) An apparatus for fabricating a III-V nitride film including at least Al on a given substrate using a Hydride Vapor Phase Epitaxy method using a chloride-based gas, comprising a double reactor structure constructed of an inner reactor to hold a substrate and at least an aluminum metallic material therein and an outer reactor surrounding the inner reactor comprising a silicon oxide-based material, the inner reactor and the outer reactor being spaced from one another, and an evacuation system in communication with a space between the inner reactor and the outer reactor being evacuated and maintained in vacuum, a gas-supplying means to introduce chloride-based gas, ammonia gas and carrier gas into the inner reactor, a heater to heat the interior of the inner reactor, and a gas leak-detecting means with a gas concentration sensor to detect gas leaks between the inner reactor and the outer reactor.

9. (previously presented) A fabricating apparatus as defined in claim 8, further comprising means for generating a given pressure difference between the inner reactor and the outer reactor, and means for detecting a given gas concentration in either the inner reactor or the outer reactor which is lower in pressure, said means for detecting said given gas concentration comprising a gas concentration sensor.